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## 捷多邦,专业PCBF**SN54AB和5401 \$ SN74ABT5401 11-BIT LINE/MEMORY DRIVERS WITH 3-STATE OUTPUTS** SCBS235B – JUNE 1992 – REVISED JANUARY 1997

- Output Ports Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art *EPIC-*II*B*<sup>™</sup> BiCMOS Design Significantly Reduces Power Dissipation
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Typical V<sub>OLP</sub> (Output Ground Bounce) < 1 V at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C
- Typical V<sub>OLV</sub> (Output Undershoot) < 0.5 V at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C
- Package Options Include Plastic
  Small-Outline (DW) Package, Ceramic Chip Carriers (FK), and DIPs (JT)

## description

These 11-bit buffers and line drivers are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

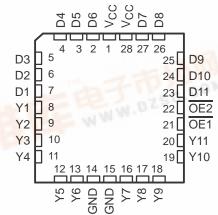
The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable  $(\overline{OE1} \text{ or } \overline{OE2})$  input is high, all 11 outputs are in the high-impedance state. These devices provide inverted data.

The outputs, which are designed to source or sink up to 12 mA, include equivalent  $25-\Omega$  series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

SN54ABT5401 JT PACKAGE SN74ABT5401 DW PACKAGE (TOP VIEW)									
Y1 [ Y2 [ Y3 [ Y4 [ Y5 [ Y6 [	1 2 3 4 5 6	28 27 26 25 24 23	D1 D2 D3 D4 D5 D6						
GND [ GND ] Y7 [ Y8 ] Y10 ] Y11 [ OE1 ]	7 8 9 10 11 12 13 14	22 21 20 19 18 17 16 15	V <sub>CC</sub> D7 D8 D9 D10 D11 OE2						

### SN54ABT5401 . . . FK PACKAGE (TOP VIEW)



The SN54ABT5401 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT5401 is characterized for operation from –40°C to 85°C.

	FUNCTION TABLE								
	15	INPUTS	OUTPUT						
1	OE1	OE2	D	Y					
	0.0	L	L	Н					
-	L	L	Н	L					
	Н	Х	Х	Z					
	Х	Н	Х	Z					



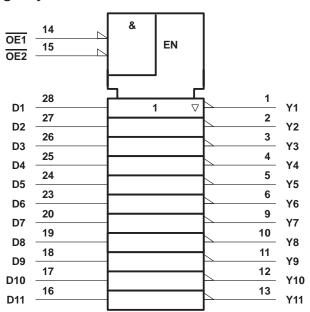
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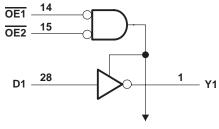


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## logic symbol<sup>†</sup>



## logic diagram (positive logic)



**To Ten Other Channels** 

<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

Pin numbers shown are for the DW and JT packages.

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>‡</sup>

Supply voltage range, V <sub>CC</sub> Input voltage range, V <sub>I</sub> (see Note 1)	
Voltage range applied to any output in the high or power-off state, VO	–0.5 V to 5.5 V
Current into any output in the low state, IO	30 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–18 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Package thermal impedance, $\theta_{JA}$ (see Note 2): DW package	
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.



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## recommended operating conditions (see Note 3)

				BT5401	SN74ABT5401		UNIT
			MIN	MAX	MIN	MAX	UNIT
V <sub>CC</sub> Supply voltage				5.5	4.5	5.5	V
V <sub>IH</sub> High-level input voltage				15	2		V
VIL	VIL Low-level input voltage					0.8	V
V <sub>I</sub> Input voltage				Vcc	0	VCC	V
IOH High-level output current				-12		-12	mA
IOL	IOL Low-level output current					12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled	44	10		10	ns/V
TA	T <sub>A</sub> Operating free-air temperature				-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T <sub>A</sub> = 25°C			SN54ABT5401		SN74ABT5401			
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	UNIT	
VIK		V <sub>CC</sub> = 4.5 V,	lj = -18 mA			-1.2		-1.2		-1.2	V	
		V <sub>CC</sub> = 4.5 V,	$I_{OH} = -1 \text{ mA}$	3.35	3.7		3.3		3.35		v	
Varia		V <sub>CC</sub> = 5 V,	$I_{OH} = -1 \text{ mA}$	3.85	4.2		3.8		3.85			
VOH		V <sub>CC</sub> = 4.5 V	$I_{OH} = -3 \text{ mA}$				3		3.1			
		VCC = 4.5 V	I <sub>OH</sub> = -12 mA	2.6					2.6			
Val			I <sub>OL</sub> = 8 mA					0.8		0.65	V	
VOL		$V_{CC} = 4.5 V$	I <sub>OL</sub> = 12 mA							0.8	v	
V <sub>hys</sub>					100						mV	
Ц		V <sub>CC</sub> = 5.5 V,	$V_I = V_{CC}$ or GND			±1		±1		±1	μA	
IOZH		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 2.7 V			50		50		50	μA	
IOZL		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 0.5 V			-50		-50		-50	μA	
loff		V <sub>CC</sub> = 0,	$V_{I} \text{ or } V_{O} \le 4.5 \text{ V}$			±100		41		±100	μA	
ICEX		V <sub>CC</sub> = 5.5 V, V <sub>O</sub> = 5.5 V	Outputs high			50	10 <sup>7</sup>	50		50	μΑ	
IO		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 2.5 V	-25	-45	-100	-25	-100	-25	-100	mA	
los‡		V <sub>CC</sub> = 5.5 V,	$V_{O} = 0$	-50		-200	50	-200	-50	-200	mA	
		V <sub>CC</sub> = 5.5 V,	Outputs high		5	50		50		50	μA	
ICC		$I_{O} = 0,$	Outputs low		36	45		45		45	mA	
		$V_I = V_{CC}$ or GND	Outputs disabled		1	50		50		50	μA	
	Data inputs		V <sub>CC</sub> = 5.5 V, One input at 3.4 V,	Outputs enabled			1.5		1.5		1.5	
7ICC§		· · · · · · · · · · · · · · · · · · ·	Outputs disabled			0.05		0.05		0.05	mA	
	Control inputs	$V_{CC}$ = 5.5 V, One input at 3.4 V, Other inputs at V <sub>CC</sub> or GND				1.5		1.5		1.5		
Ci	C <sub>i</sub> V <sub>I</sub> = 2.5 V or 0.5 V			3						pF		
Co	$C_0$ V <sub>O</sub> = 2.5 V or 0.5 V			8						pF		

<sup>†</sup> All typical values are at  $V_{CC} = 5 V$ .

<sup>‡</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.



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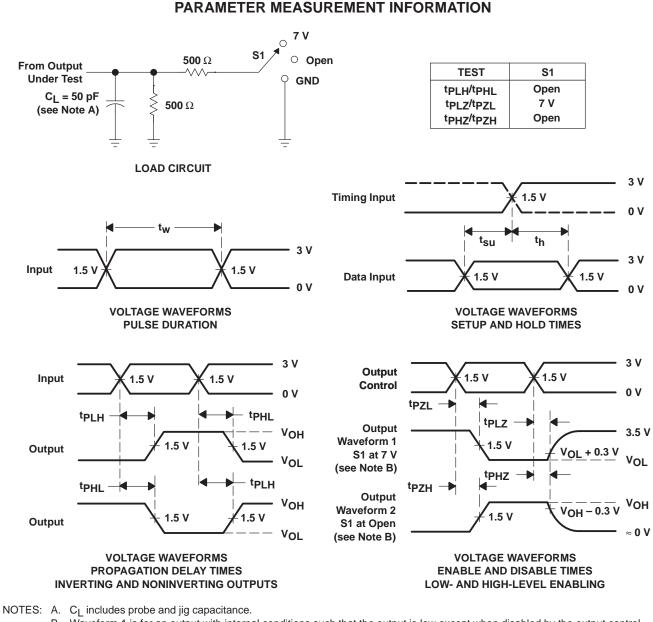
# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)			CC = 5 V A = 25°C	;	SN54AB	T5401	SN74AB	T5401	UNIT
	(INFOT)	(001201)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<sup>t</sup> PLH	D	Y	2	4.5	6.1	2	47	2	6.9	ns
<sup>t</sup> PHL			1.5	4.4	5.2	1.5	5.9	1.5	5.7	
<sup>t</sup> PZH	ŌĒ	Y	2.5	5.7	6.6	2.5	8.6	2.5	8.5	20
<sup>t</sup> PZL			2	4.4	5.5	Z	6.9	2	6.8	ns
<sup>t</sup> PHZ	ŌĒ	v	1.5	3.6	4.4	<b>1</b> .5	5.5	1.5	5.2	200
<sup>t</sup> PLZ			1.5	4.2	5.4	<b>2</b> 1.5	7.4	1.5	6.9	ns



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- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>Q</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 n
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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